

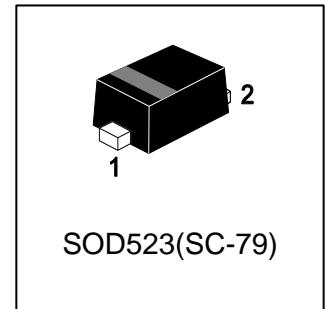
L1SS400T1G

S-L1SS400T1G

Switching Diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Extremely small surface mounting type.
- High Speed.
- High reliability.



2. APPLICATIONS

- High speed switching.

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L1SS400T1G	A	3000/Tape&Reel
L1SS400T3G	A	10000/Tape&Reel

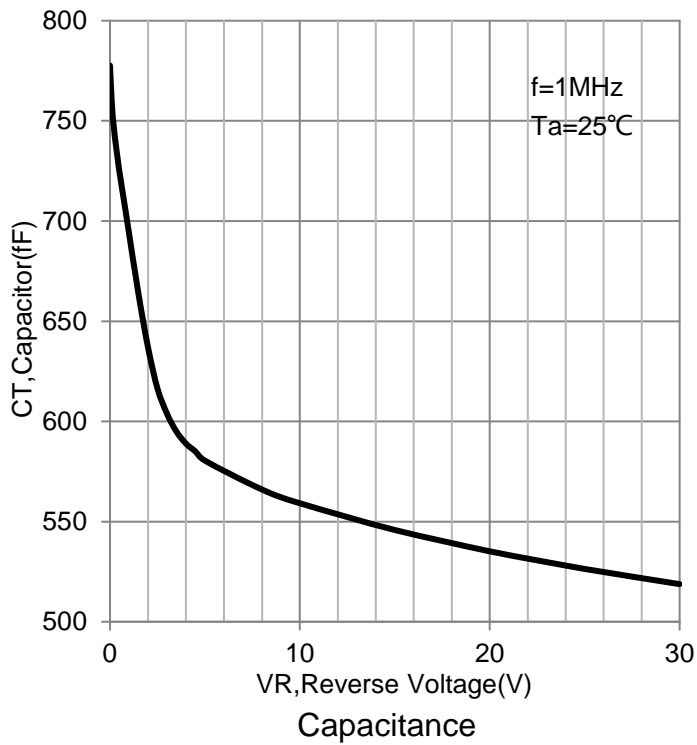
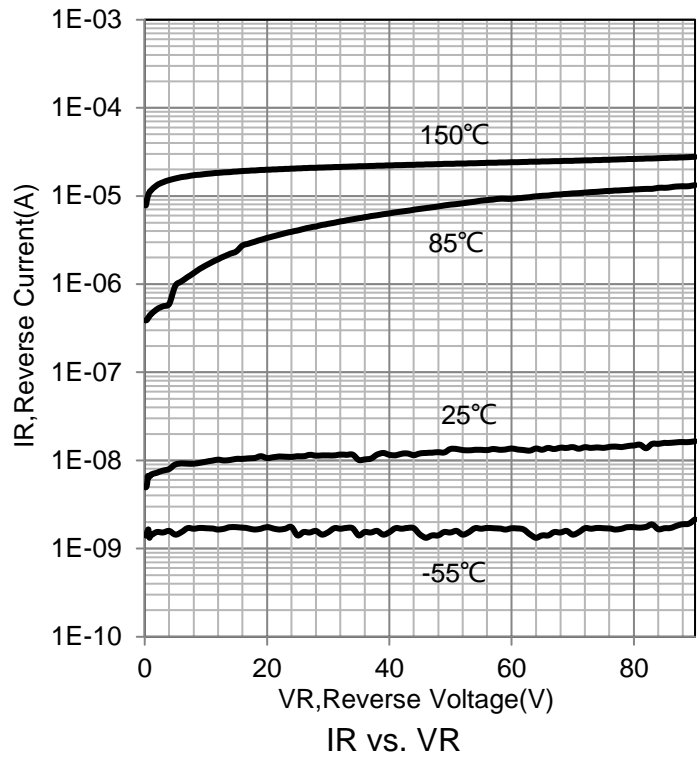
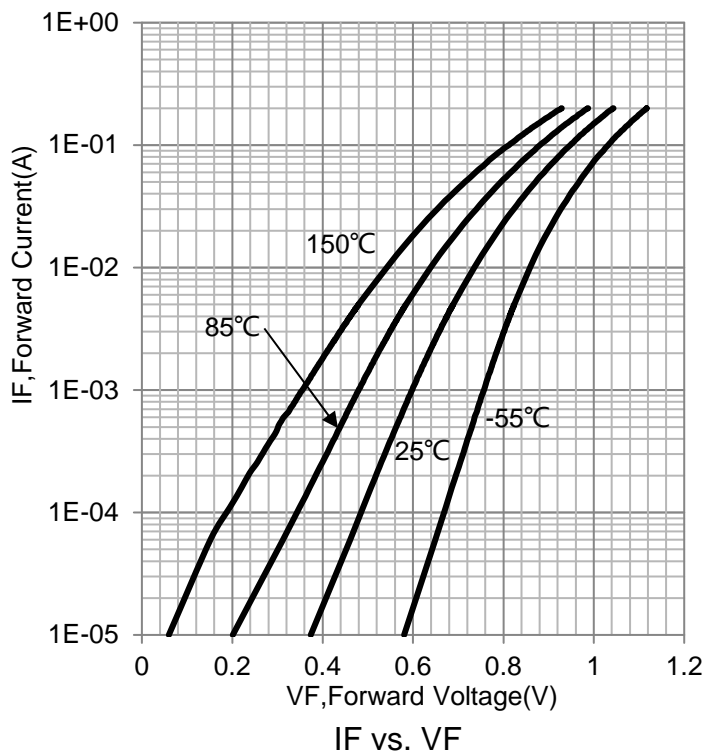
4. MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Limit	Unit
Peak reverse voltage	VRM	90	V
DC reverse voltage	VR	80	V
Peak forward current	IFM	225	mA
Mean rectifying current	IO	100	mA
Surge current (1s)	Is	500	mA
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C

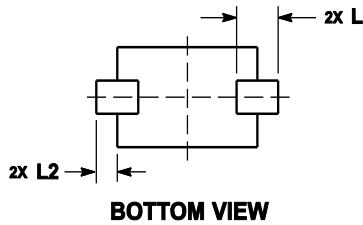
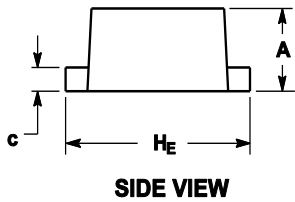
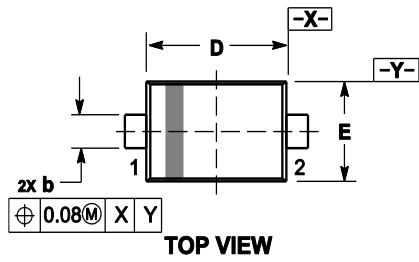
5. ELECTRICAL CHARACTERISTICS (Tj = 25°C unless otherwise specified.)

Parameter	Symbol	Min	Typ.	Max	Unit
Forward voltage (IF = 100mA)	VF	-	-	1.2	V
Reverse current (VR = 80V)	IR	-	-	0.1	μA
Capacitance between terminals (VR = 0.5V, f = 1MHz)	CT	-	0.72	3	pF
Reverse recovery time (VR = 6V, IF = 10mA, RL = 100Ω)	trr	-	-	4	ns

6.ELECTRICAL CHARACTERISTICS CURVES



7. OUTLINE AND DIMENSIONS



Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.60	0.70	0.020	0.024	0.028
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.07	0.14	0.20	0.003	0.006	0.008
D	1.10	1.20	1.30	0.043	0.047	0.051
E	0.70	0.80	0.90	0.028	0.031	0.035
H _E	1.50	1.60	1.70	0.059	0.063	0.067
L	0.30 REF			0.012 REF		
L ₂	0.15	0.20	0.25	0.006	0.008	0.010

8. SOLDERING FOOTPRINT

